ON Semiconductor

Final Product/Process Change Notification

Document # : FPCN20832
Issue Date: 17 March 2015

Title of Change:	Trench 6 Technology Capacity Expansion by Qualification of ON Semiconductor's wafer fab in Pocatello, ID
Proposed first ship date:	24 June 2015
Contact information:	Contact your local ON Semiconductor Sales Office or Jason Jeong <Jason.jeong@onsemi.com>
Samples:	Contact your local ON Semiconductor Sales Office or Michael Mooney <fg6h9j@onsemi.com>
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or Donna Scheuch <d.scheuch@onsemi.com>.
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <PCN.Support@onsemi.com>.
Change Part Identification:	The affected products listed here with date code 1523 and later will dual sourced out of ON Semiconductor's Wafer fab in Gresham and Pocatello.

Change category(s):

☒ Wafer Fab Change
☐ Assembly Change
☐ Test Change
☐ Manufacturing Site Change/Addition
☐ Manufacturing Process Change
☐ Material Change
☐ Product specific change
☐ Datasheet/Product Doc change
☐ Shipping/Packaging/Marking
☐ Other: _____

Sites Affected:	Site 1	Site 2
☐ All site(s) ☐ not applicable ☒ ON Semiconductor site(s) : ☐ External Foundry/Subcon site(s):	ON Pocatello, Idaho	

Description and Purpose:

This final change notification is to inform customers of ON Semiconductor's plan to qualify and add capacity in FAB10 for the 30V Trench (T6) MOSFET technology. FAB10 is an internal wafer fab within ON Semiconductor located in Pocatello, ID. At the expiration of this notification, all products listed here will be dual sourced from its current ON Semiconductor wafer fab in Gresham and FAB10.

Reliability Qualification and full electrical characterization over temperature have been performed, and available upon request.

Reliability Data Summary:

NTMFS4C05NT1G

Package: SO8FL

Test	Specification	Conditions	Interval	Sample Size	Results
HTRB	JESD22-A108	Ta=150°C, 80% max rated Vdss	504 hrs	84pc/3 lots	0/252
HTGB	JESD22-A108	Ta=150°C, 100% max rated Vgss	504 hrs	84pc/3 lots	0/252
HTSL	JESD22-A103	Ta=150°C	504 hrs	84pc/3 lots	0/252
IOL	MIL-STD-750 (M 1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off = 2 min	7500 cyc	84pc/3 lots	0/252
TC	JESD22-A104	Ta=-65°C to +150°C	500 cyc	84pc/3 lots	0/252
HAST	JESD22-A110	131°C/85% RH, 85% max rated Vdss	96 hrs	84pc/3 lots	0/252
uHAST	JESD22-A118	131°C/85% RH, 85% max rated Vdss	96 hrs	84pc/3 lots	0/252

NTTFS4C05NTAG

Package: u8FL

Test	Specification	Conditions	Interval	Sample Size	Results
HTRB	JESD22-A108	Ta=150°C, 80% max rated Vdss	504 hrs	84pc/1 lots	0/84
HTGB	JESD22-A108	Ta=150°C, 100% max rated Vgss	504 hrs	84pc/1 lots	0/84
HTSL	JESD22-A103	Ta=150°C	504 hrs	84pc/1 lots	0/84
IOL	MIL-STD-750 (M 1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off = 2 min	7500 cyc	84pc/1 lots	0/84
TC	JESD22-A104	Ta=-65°C to +150°C	500 cyc	84pc/1 lots	0/84
H3TRB	JESD22-A101	85°C, 85% max rated Vdss	504 hrs	84pc/1 lots	0/84
uHAST	JESD22-A118	131°C, 85% max rated Vdss	96 hrs	84pc/1 lots	0/84

Electrical Characteristic Summary:

There is no change in electrical parametric performance. Characterization data is available upon request.

List of Affected Standard Parts:

NTMFS4C05NT1G	NTTFS4C10NTAG	NTTFS4C10NTWG
NTMFS4C05NT3G	NTMFS4C08NT1G	NTMFS4C13NT1G
NTTFS4C05NTAG	NTMFS4C08NT3G	NTMFS4C13NT3G
NTTFS4C05NTWG	NTTFS4C08NTAG	NTTFS4C13NTAG
NTMFS4C06NT1G	NTMFS4C09NT1G	NTTFS4C13NTWG
NTTFS4C06NTAG	NTMFS4C09NT3G	
NTTFS4C06NTWG	NTMFS4C10NT1G	

NOTE: Please be informed that parts impacted by this PDN/PCN are Special/Customer specific parts, thus MPN & CPN info will be available to affected customers only by clicking the "Custom PCN for Selected Company Button" in the Document Analysis page of PCMS/PCN Alert.